

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3537	"trench capacitor" or "trench-capacitor"	US-PGPUB; USPAT	OR	ON	2005/02/17 10:54
L2	873	((lower or first or bottom) with (electrode or plate)) with (dop\$ with trench)	US-PGPUB; USPAT	OR	ON	2005/02/17 10:54
L3	681002	(upper or second or top) with (electrode or plate)	US-PGPUB; USPAT	OR	ON	2005/02/17 10:56
L4	489	L2 with L3	US-PGPUB; USPAT	OR	ON	2005/02/17 10:55
L5	204	L1 and L4	US-PGPUB; USPAT	OR	ON	2005/02/17 10:56
L6	3906956	@ad<"20021129"	US-PGPUB; USPAT	OR	ON	2005/02/17 10:56
L7	142	L5 and L6	US-PGPUB; USPAT	OR	ON	2005/02/17 10:56
L8	1746	((upper or second or top) with (electrode or plate)) with (Ru or ruthenium)	US-PGPUB; USPAT	OR	ON	2005/02/17 11:13
L9	1	2 with 8	US-PGPUB; USPAT	OR	ON	2005/02/17 10:57
L10	1	2 same 8	US-PGPUB; USPAT	OR	ON	2005/02/17 10:57
L11	4	2 and 8	US-PGPUB; USPAT	OR	ON	2005/02/17 10:58
L12	3	11 not 10	US-PGPUB; USPAT	OR	ON	2005/02/17 11:07
L13	63907	Ru or ruthenium	US-PGPUB; USPAT	OR	ON	2005/02/17 11:07
L14	3	12 and 13	US-PGPUB; USPAT	OR	ON	2005/02/17 11:08
L15	1	("20040036102").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/17 11:08
L16	1	13 and 15	US-PGPUB; USPAT	OR	ON	2005/02/17 11:09
L17	2	6 and 14	US-PGPUB; USPAT	OR	ON	2005/02/17 11:09
L18	137	((upper or second or top) with (electrode or plate)) with ((Ru or ruthenium) with (poly or polysilicon or "poly-silicon"or "poly silicon" or "poly-Si" or "poly Si" or "polycrystalline-silicon" or "polycrystalline silicon" or "polycrystalline-Si" or "polycrystalline Si"))	US-PGPUB; USPAT	OR	ON	2005/02/17 11:17

L19	2	2 and 18	US-PGPUB; USPAT	OR	ON	2005/02/17 11:18
L20	0	6 and 19	US-PGPUB; USPAT	OR	ON	2005/02/17 11:18
L21	11	1 and 18	US-PGPUB; USPAT	OR	ON	2005/02/17 11:19
L22	6	6 and 21	US-PGPUB; USPAT	OR	ON	2005/02/17 11:19